

isc Silicon PNP Darlington Power Transistor

2SB1340

DESCRIPTION

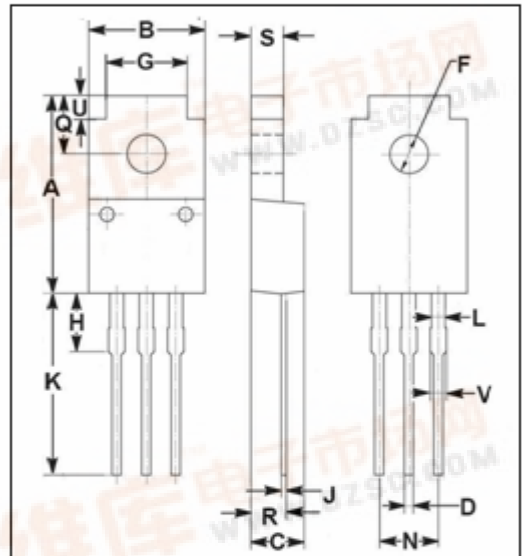
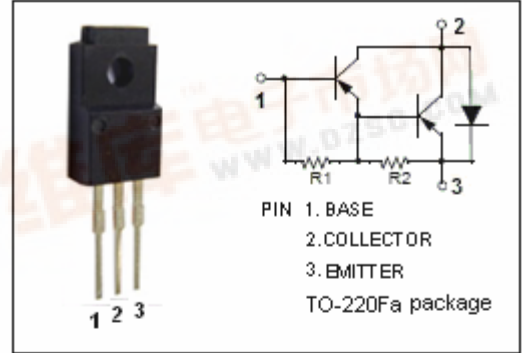
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -120V(\text{Min})$
- High DC Current Gain-
: $h_{FE} = 2000(\text{Min}) @ (V_{CE} = -3V, I_C = -2A)$
- Complement to Type 2SD1889

APPLICATIONS

- Designed for power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|------------------|
| V_{CBO} | Collector-Base Voltage | -120 | V |
| V_{CEO} | Collector-Emitter Voltage | -120 | V |
| V_{EBO} | Emitter-Base Voltage | -6 | V |
| I_C | Collector Current-Continuous | -6 | A |
| I_{CM} | Collector Current-Peak | -10 | A |
| P_C | Collector Power Dissipation @ $T_a=25^\circ\text{C}$ | 2 | W |
| | Collector Power Dissipation @ $T_C=25^\circ\text{C}$ | 30 | |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature | -55~150 | $^\circ\text{C}$ |



| DIM | mm | |
|-----|-------|-------|
| | MIN | MAX |
| A | 16.85 | 17.15 |
| B | 9.90 | 10.10 |
| C | 4.35 | 4.65 |
| D | 0.75 | 0.80 |
| F | 3.20 | 3.40 |
| G | 6.90 | 7.10 |
| H | 5.15 | 5.45 |
| J | 0.45 | 0.75 |
| K | 13.35 | 13.65 |
| L | 1.10 | 1.30 |
| N | 4.98 | 5.18 |
| Q | 4.85 | 5.15 |
| R | 2.95 | 3.25 |
| S | 2.70 | 2.90 |
| U | 1.75 | 2.05 |
| V | 1.30 | 1.50 |



isc Silicon PNP Darlington Power Transistor**2SB1340****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|------|------|-------|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = -5mA ; I _B = 0 | -120 | | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = -50 μ A ; I _E = 0 | -120 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = -3A; I _B = -6mA | | | -1.5 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = -120V ; I _E = 0 | | | -100 | μ A |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = -5V; I _C = 0 | | | -3 | mA |
| h _{FE} | DC Current Gain | I _C = -2A ; V _{CE} = -3V | 2000 | | 20000 | |
| C _{OB} | Output Capacitance | I _E = 0; V _{CB} = -10V; f _{test} = 1MHz | | 70 | | pF |
| f _T | Current-Gain—Bandwidth Product | I _E = 0.5A ; V _{CE} = -5V; f _{test} = 10MHz | | 12 | | MHz |